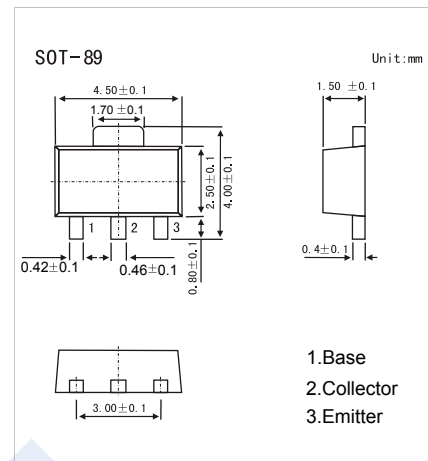


## PNP Transistors

## KTA1664

## ■ Features

- 1W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to KTC4376

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-35	V
Collector - Emitter Voltage	$V_{CE0}$	-30	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-800	mA
Base Current	$I_B$	-160	
Collector Power Dissipation	$P_C$	500	mW
		1	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -1\text{ mA}, I_E = 0$	-35			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -10\text{ mA}, I_B = 0$	-30			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -1\text{ mA}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -35\text{ V}, I_E = 0$			-0.1	uA
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -5\text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -20\text{ mA}$			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{ mA}, I_B = -20\text{ mA}$			-1.2	
Base - emitter voltage	$V_{BE}$	$V_{CE} = -1\text{ V}, I_C = -10\text{ mA}$			-0.8	
DC current gain	$h_{FE}$	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	100		320	
		$V_{CE} = -1\text{ V}, I_C = -700\text{ mA}$	35			
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		19		pF
Transition frequency	$f_T$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$		120		MHz

■ Classification of  $h_{FE}(1)$ 

Type	KTA1664-O	KTA1664-Y
Range	100-200	160-320
Marking	RO	RY

### PNP Transistors

### KTA1664

■ Typical Characteristics

